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Kind regards,

Team Nexperia



PMBT4401YS

40 V, 600 mA, double NPN switching transistor

2 July 2015

Product data sheet

1. General description

Double NPN switching transistor in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package.

Double PNP complement: PMBT4403YS

2. Features and benefits

- Double general-purpose switching transistor
- High current (max. 600 mA)
- Voltage max. 40 V
- AEC-Q101 qualified

3. Applications

- Switching and linear amplification

4. Quick reference data

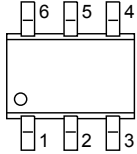
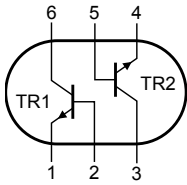
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{CE0}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current		-	-	600	mA
Per transistor						
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}; I_C = 150\text{ mA}; t_p \leq 300\text{ }\mu\text{s};$ $\delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	100	-	300	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; t_p \leq 300\text{ }\mu\text{s};$ $\delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	40	-	-	



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter TR1	 <p>TSSOP6 (SOT363)</p>	 <p><i>sym020</i></p>
2	B	base TR1		
3	C	collector TR2		
4	E	emitter TR2		
5	B	base TR2		
6	C	collector TR1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBT4401YS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code
PMBT4401YS	BG% [1]

[1] % = placeholder for manufacturing site code

8. Limiting values

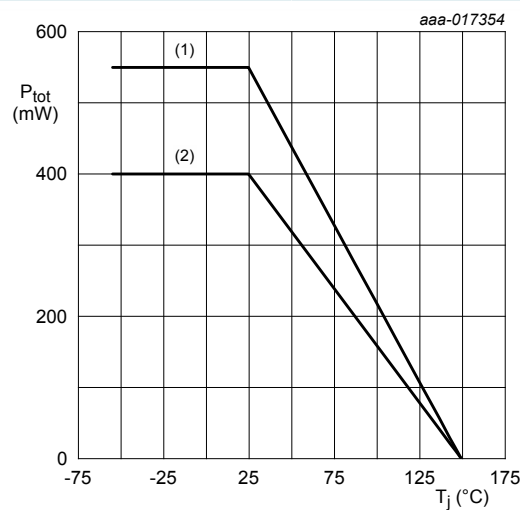
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V _{CB0}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	600	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	800	mA
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
			[2]	-	300	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	400	mW
			[2]	-	550	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm².



(1) FR4 PCB; mounting pad for collector 1 cm²
 (2) FR4 PCB; standard footprint

Fig. 1. Per device: Power derating curves SOT363 (SC-88)

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W
			[2]	-	-	417	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	313	K/W
			[2]	-	-	227	K/W

[1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm².

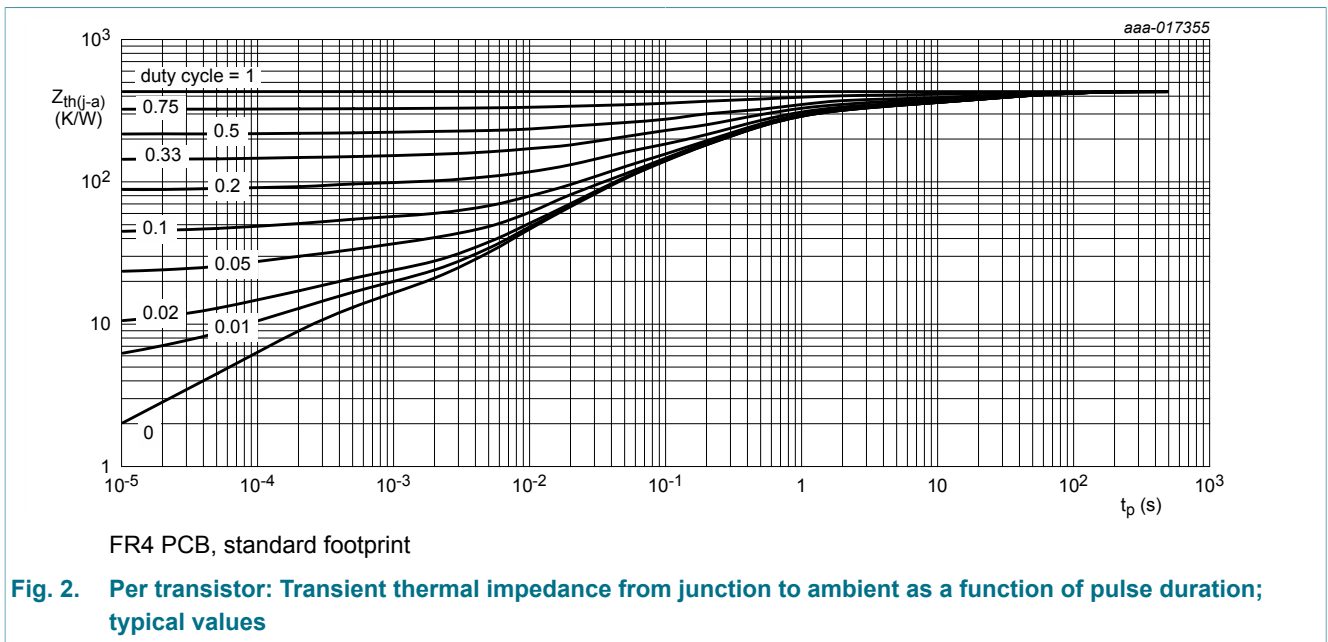
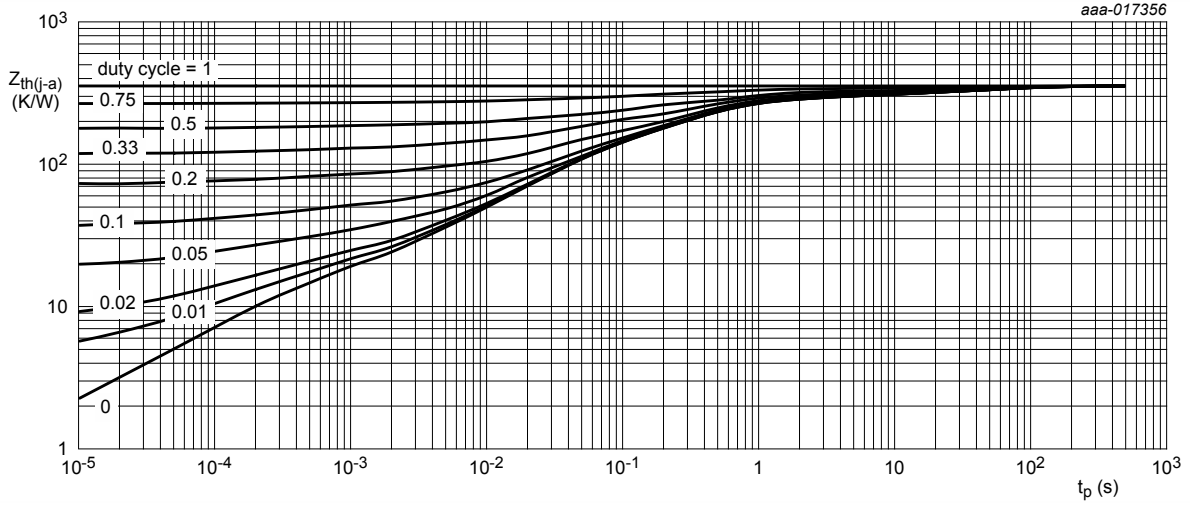


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

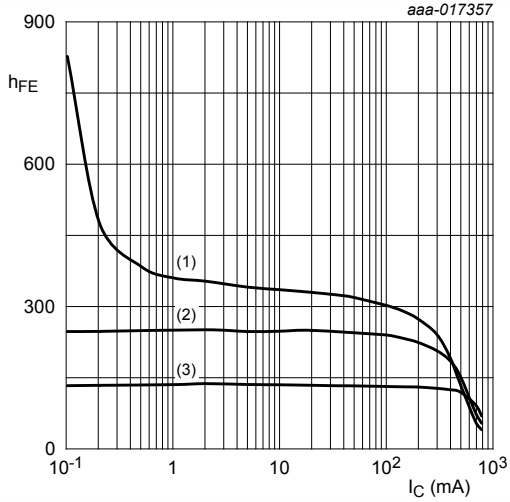


FR4 PCB, mounting pad for collector 1 cm^2
Fig. 3. Per Transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

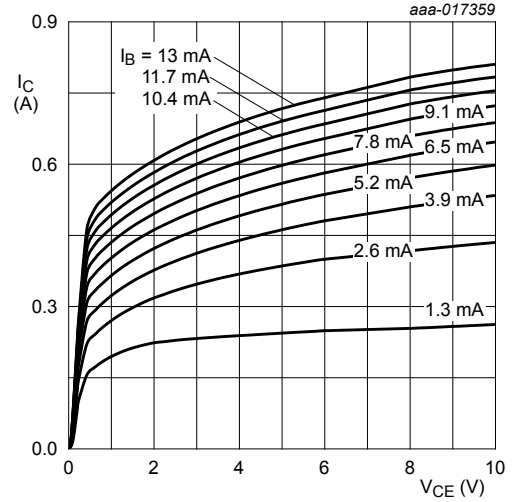
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	50	nA
		V _{CB} = 50 V; I _E = 0 A; T _j = 125 °C	-	-	10	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 6 V; I _C = 0 A; T _{amb} = 25 °C	-	-	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; I _C = 0.1 mA; T _{amb} = 25 °C	20	-	-	
		V _{CE} = 1 V; I _C = 1 mA; T _{amb} = 25 °C	40	-	-	
		V _{CE} = 1 V; I _C = 10 mA; T _{amb} = 25 °C	80	-	-	
		V _{CE} = 1 V; I _C = 150 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	100	-	300	
		V _{CE} = 2 V; I _C = 500 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	400	mV
		I _C = 500 mA; I _B = 50 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	750	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	950	mV
		I _C = 500 mA; I _B = 50 mA; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	1.2	V
t _d	delay time	I _C = 150 mA; I _{Bon} = 15 mA; I _{Boff} = -15 mA; T _{amb} = 25 °C	-	-	10	ns
t _r	rise time		-	-	25	ns
t _{on}	turn-on time		-	-	35	ns
t _s	storage time		-	-	200	ns
t _f	fall time		-	-	60	ns
t _{off}	turn-off time		-	-	250	ns
C _C	collector capacitance		V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	8
C _E	emitter capacitance	V _{EB} = 500 mV; I _C = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	30	pF
f _T	transition frequency	V _{CE} = 20 V; I _C = 20 mA; f = 100 MHz; T _{amb} = 25 °C	250	-	-	MHz
NF	noise figure	V _{CE} = 5 V; I _C = 100 μA; R _S = 1 kΩ; f = 1 kHz	-	-	4	dB



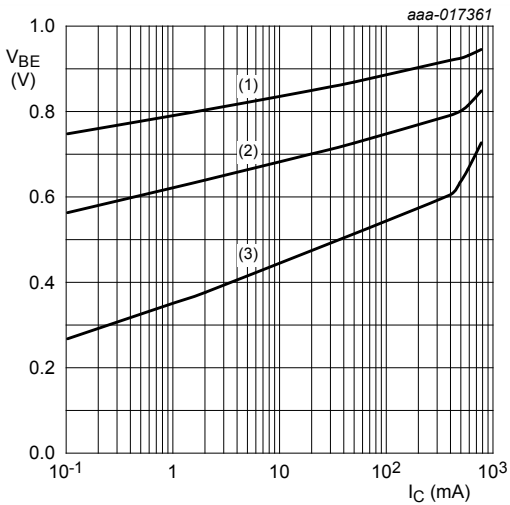
$V_{CE} = 10\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 4. DC current gain as a function of collector current; typical values



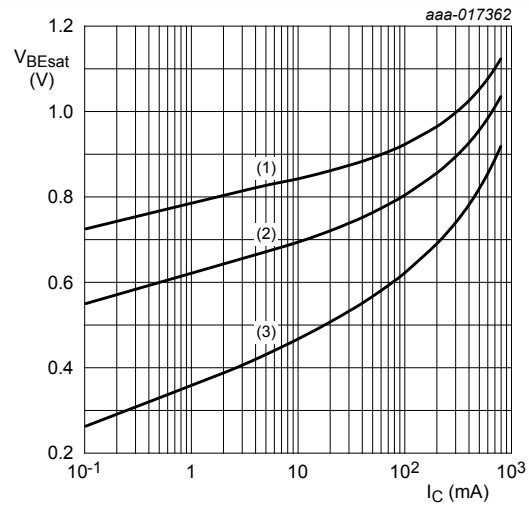
$T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 5. Collector current as a function of collector-emitter voltage; typical values



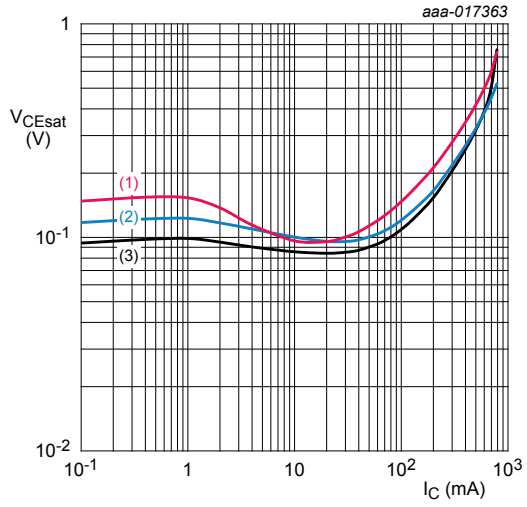
$V_{CE} = 10\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 150\text{ }^\circ\text{C}$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



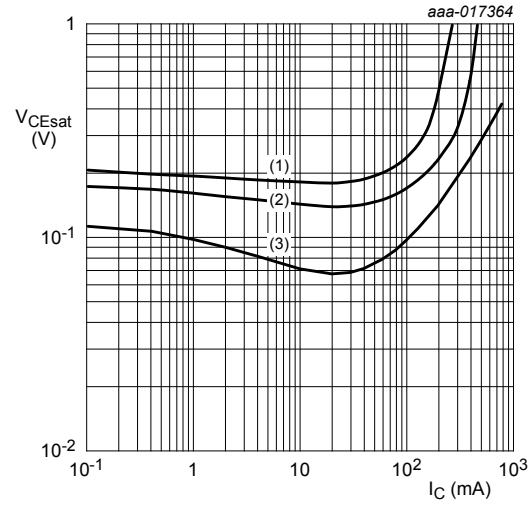
$I_C/I_B = 10$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 150\text{ }^\circ\text{C}$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150^\circ\text{C}$
 (2) $T_{amb} = 25^\circ\text{C}$
 (3) $T_{amb} = -55^\circ\text{C}$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$T_{amb} = 25^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

11. Test information

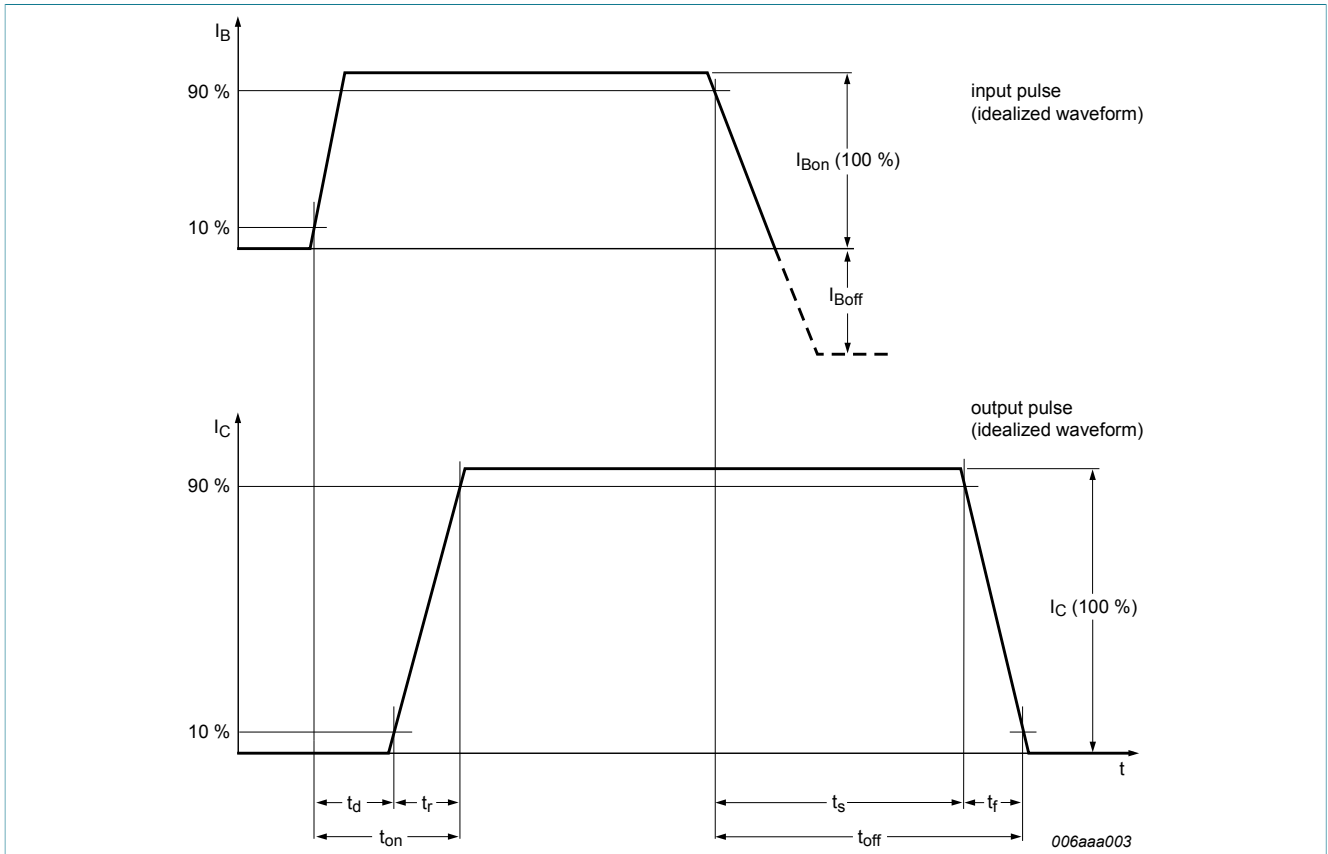


Fig. 10. BISS transistor switching time definition

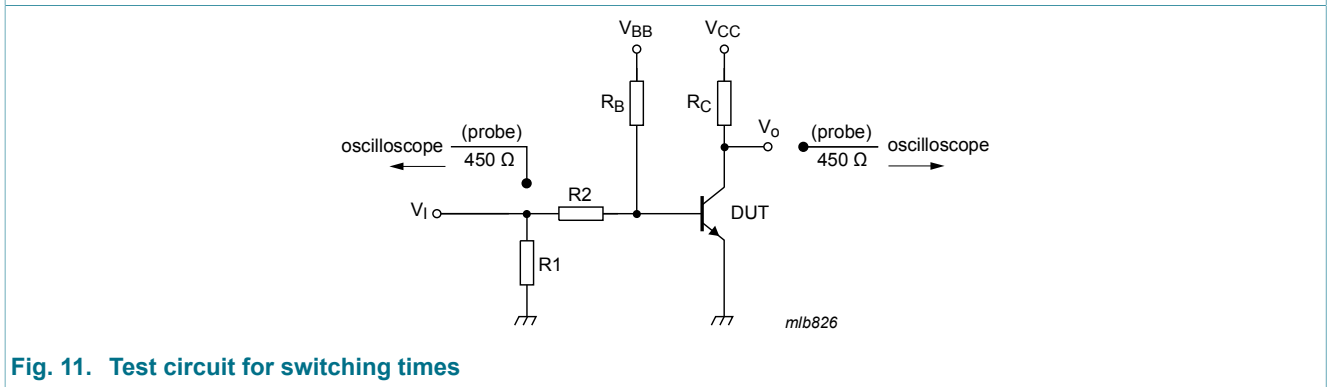


Fig. 11. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

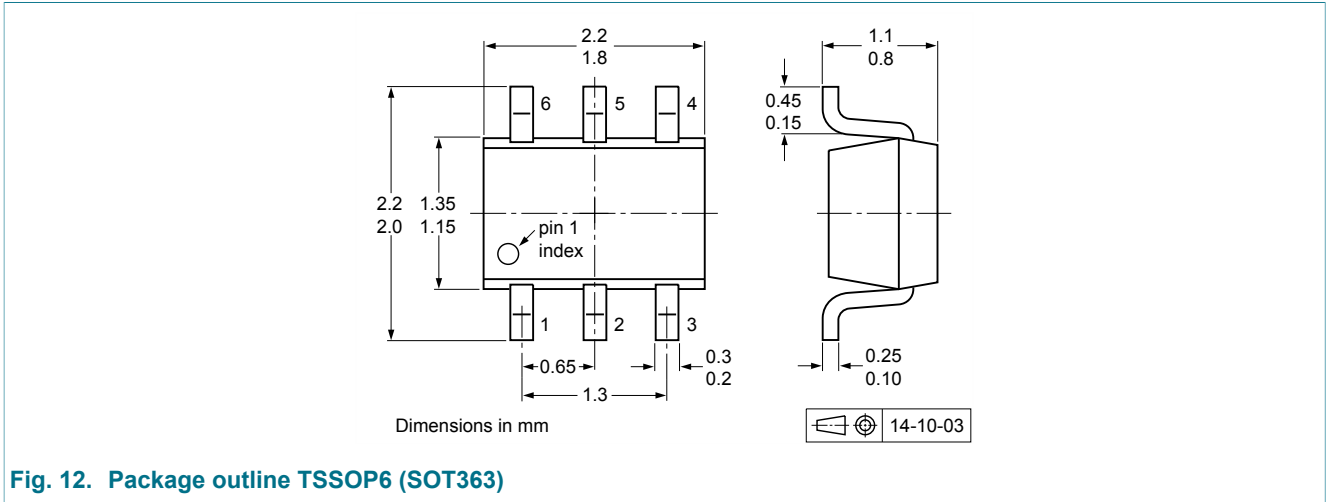


Fig. 12. Package outline TSSOP6 (SOT363)

13. Soldering

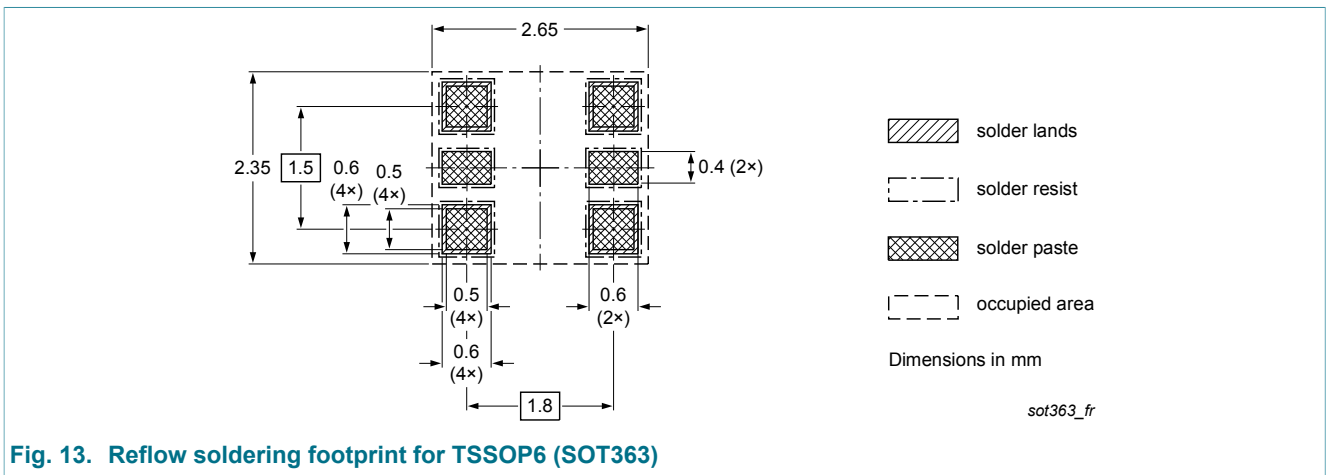


Fig. 13. Reflow soldering footprint for TSSOP6 (SOT363)

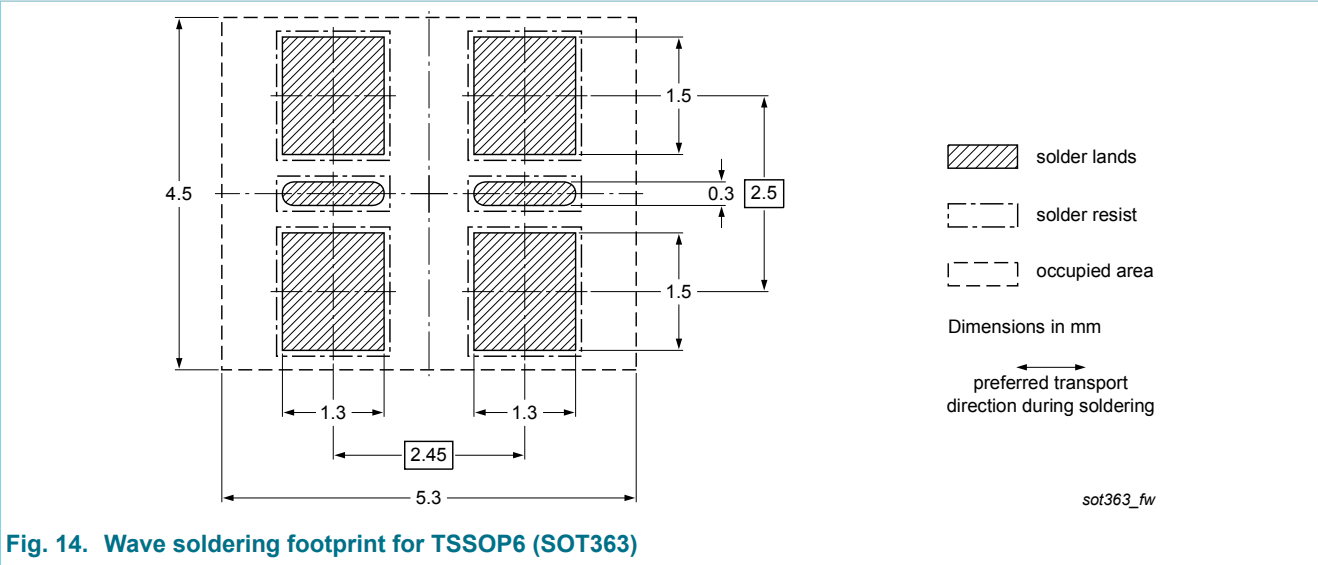


Fig. 14. Wave soldering footprint for TSSOP6 (SOT363)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMBT4401YS v.1	20150702	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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